

## N-Channel 500-V (D-S) Super Junction MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	500	
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V	0.192
$Q_g$ max. (nC)	86	
$Q_{gs}$ (nC)	9	
$Q_{gd}$ (nC)	16	
Configuration	Single	

### FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)

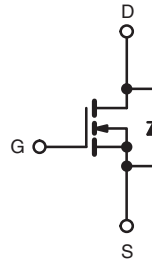
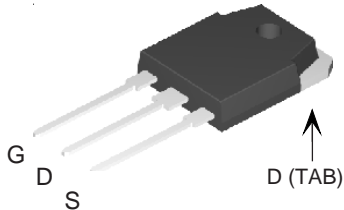
### APPLICATIONS

- Computing
  - PC silver box / ATX power supplies



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

TO-3P



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)


PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V <sub>DS</sub>	500	V
Gate-Source Voltage			V <sub>GS</sub>	± 30	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	18	A
		T <sub>C</sub> = 100 °C		12	
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	50	
Linear Derating Factor				1.25	W/°C
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	186	mJ
Maximum Power Dissipation			P <sub>D</sub>	206	W
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Drain-Source Voltage Slope	V <sub>DS</sub> = 0 V to 80 % V <sub>DS</sub>		dV/dt	70	V/ns
Reverse Diode dV/dt <sup>d</sup>		27			
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s			300	°C

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 3.1$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.

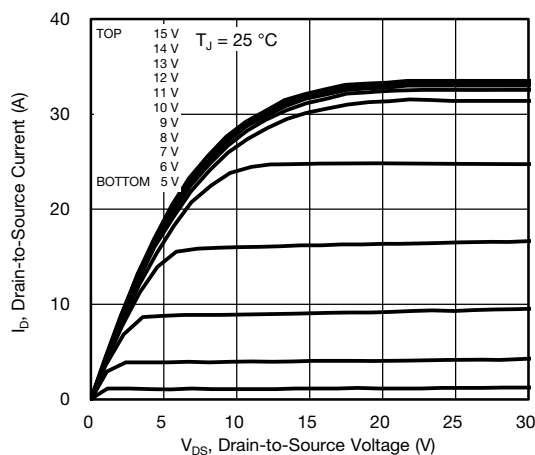
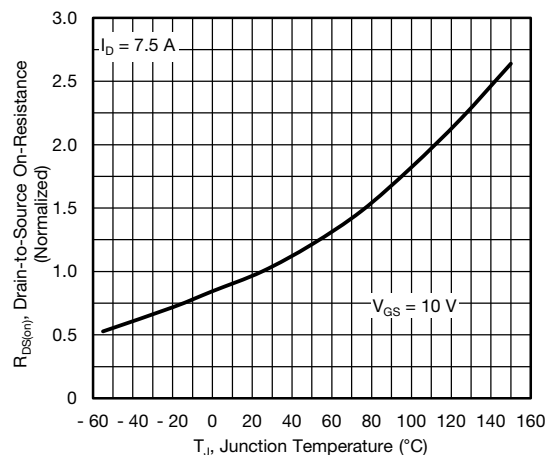
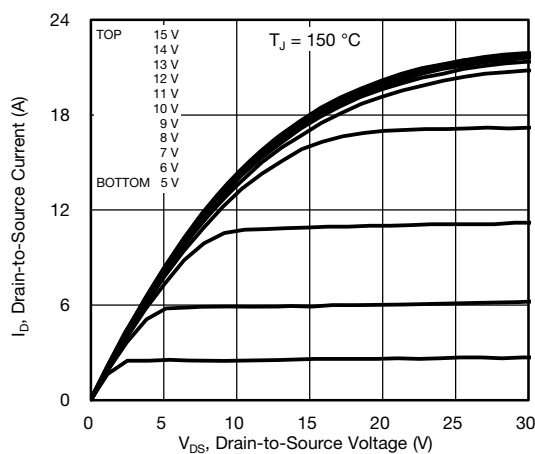
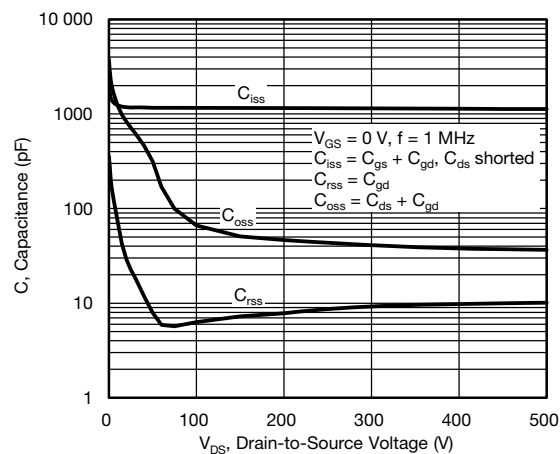
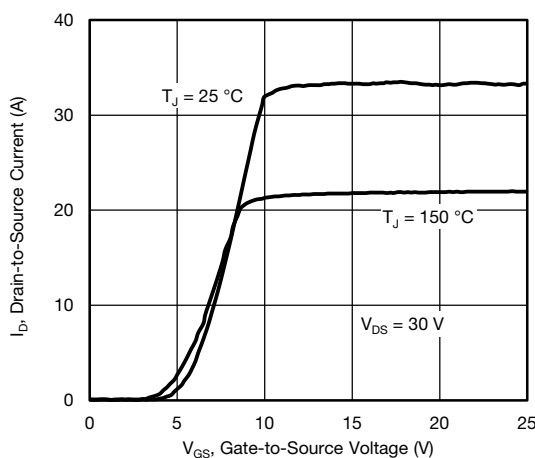
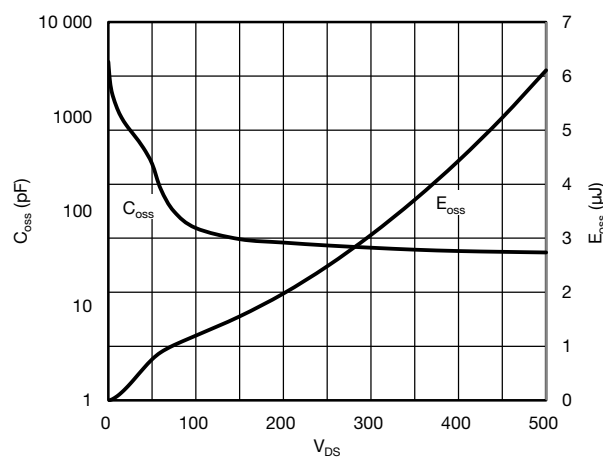
### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.8	

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		500	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.62	-	V/°C
Gate-Source Threshold Voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
		V <sub>GS</sub> = ± 30 V		-	-	± 1	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V		-	-	10	μA
		V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	25	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 9.5 A	-	0.192	-	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 30 V, I <sub>D</sub> =9.5 A		-	3.9	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 1 MHz		-	1162	-	pF
Output Capacitance	C <sub>oss</sub>			-	51	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	7	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	C <sub>o(er)</sub>	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V		-	55	-	
Effective Output Capacitance, Time Related <sup>b</sup>	C <sub>o(tr)</sub>			-	164	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 9.5 A, V <sub>DS</sub> = 400 V	-	33	66	nC
Gate-Source Charge	Q <sub>gs</sub>			-	8	-	
Gate-Drain Charge	Q <sub>gd</sub>			-	14	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 400 V, I <sub>D</sub> = 12 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 9.1 Ω		-	15	30	ns
Rise Time	t <sub>r</sub>			-	24	48	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	34	68	
Fall Time	t <sub>f</sub>			-	18	36	
Gate Input Resistance	R <sub>g</sub>	f = 1 MHz, open drain		-	0.85	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	14.5	A
Pulsed Diode Forward Current	I <sub>SM</sub>			-	-	28	
Diode Forward Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 9.5 A, V <sub>GS</sub> = 0 V		-	-	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> = 9.5 A, dI/dt = 100 A/μs, V <sub>R</sub> = 25 V		-	265	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>			-	3.2	-	μC
Reverse Recovery Current	I <sub>RRM</sub>			-	23	-	A

**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**

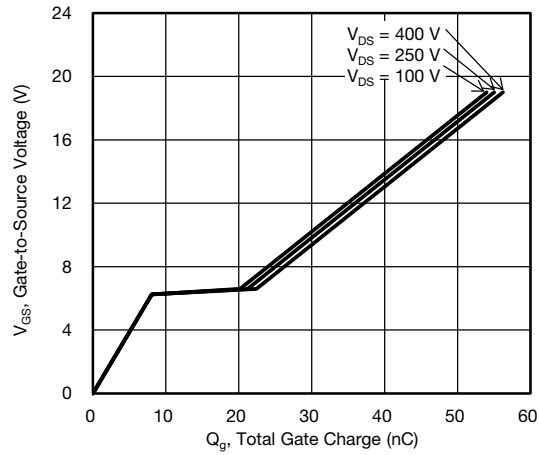


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

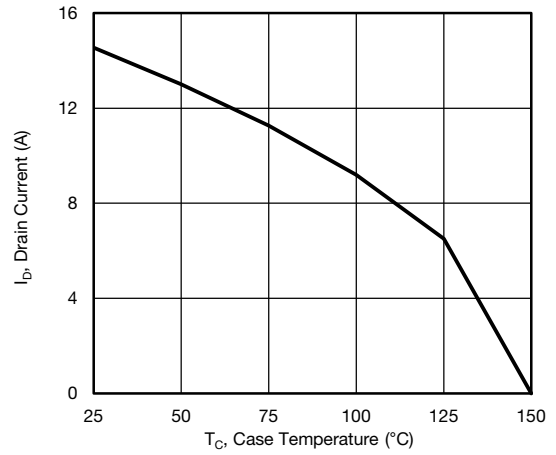


Fig. 10 - Maximum Drain Current vs. Case Temperature

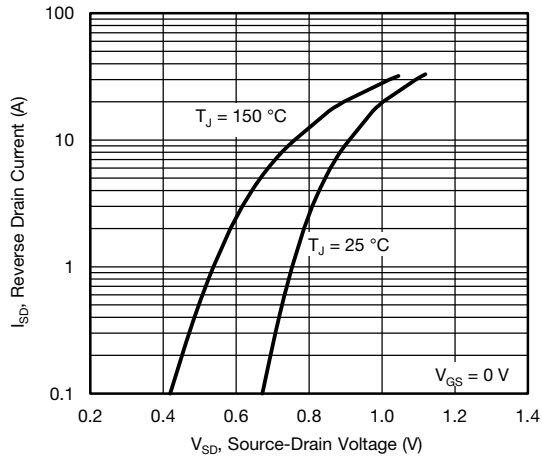


Fig. 8 - Typical Source-Drain Diode Forward Voltage

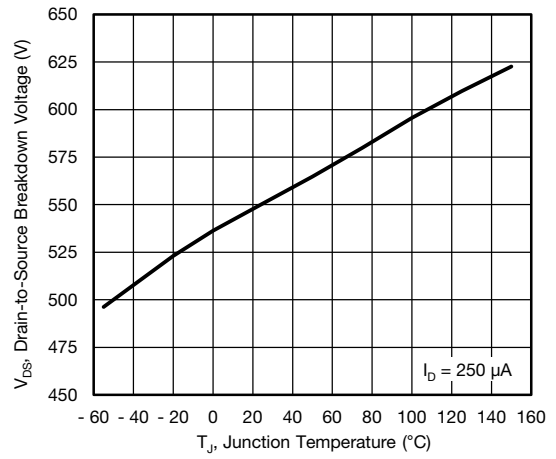


Fig. 11 - Temperature vs. Drain-to-Source Voltage

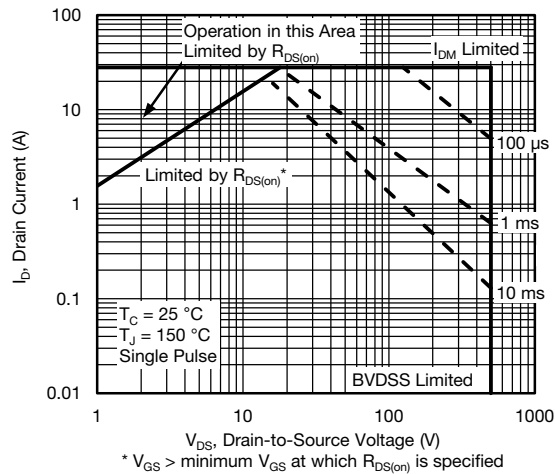
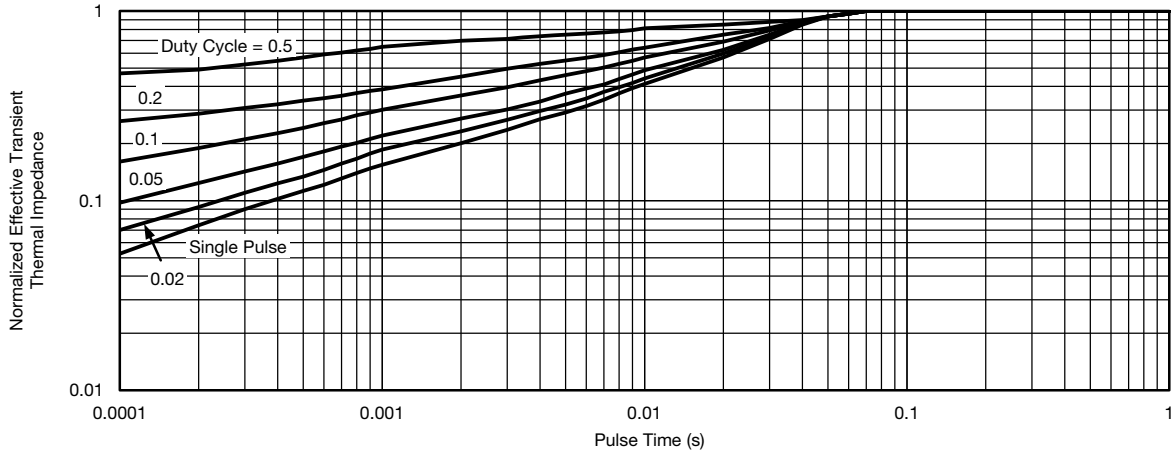
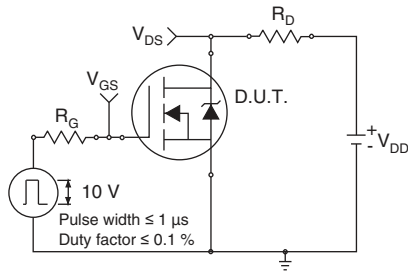


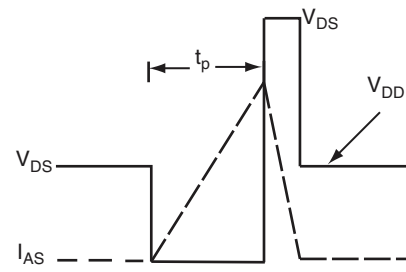
Fig. 9 - Maximum Safe Operating Area



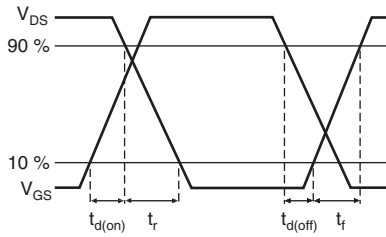
**Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case**



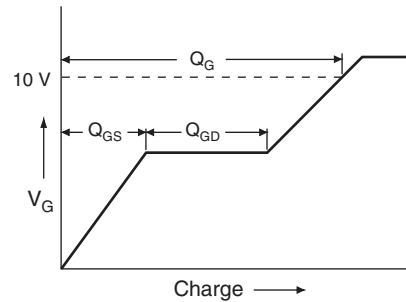
**Fig. 13 - Switching Time Test Circuit**



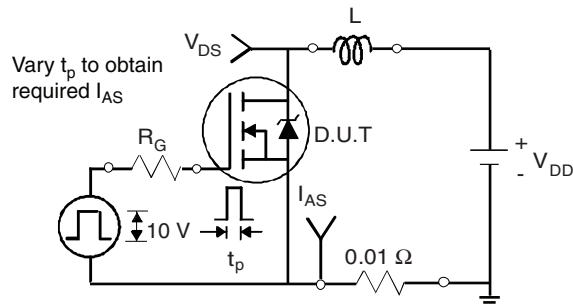
**Fig. 16 - Unclamped Inductive Waveforms**



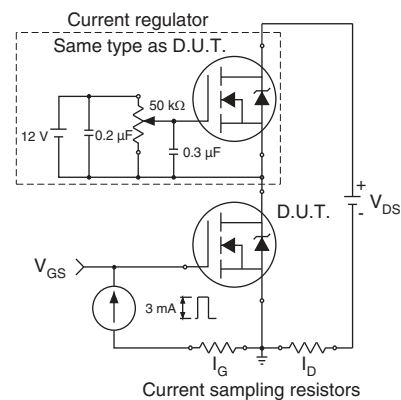
**Fig. 14 - Switching Time Waveforms**



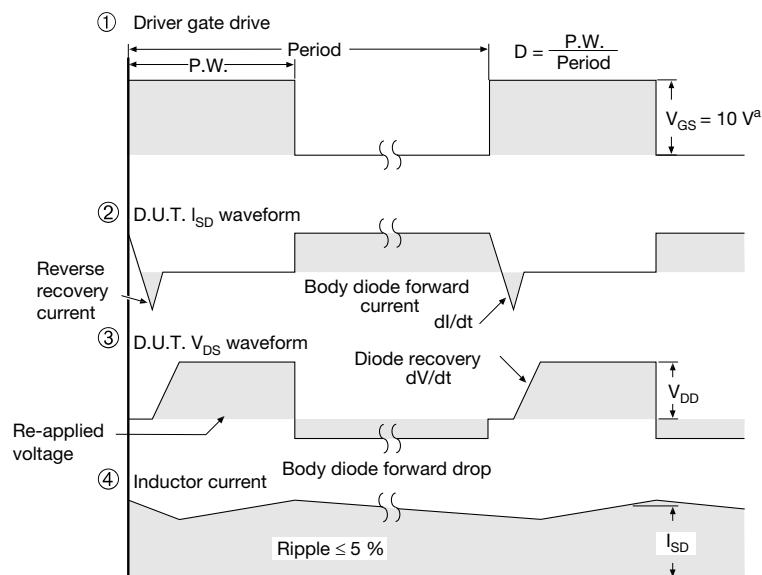
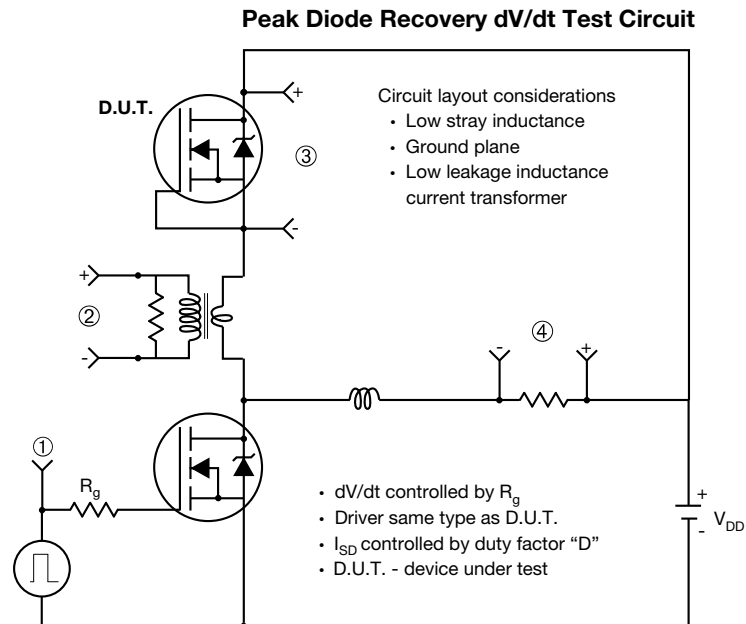
**Fig. 17 - Basic Gate Charge Waveform**



**Fig. 15 - Unclamped Inductive Test Circuit**



**Fig. 18 - Gate Charge Test Circuit**

**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 19 - For N-Channel**

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